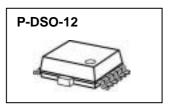


Smart High-Side Power Switch Two Channels: 2 x $90m\Omega$ Status Feedback

Product Summary

Operating Voltage	V_{bb}	5.540V		
	Active channels	one	two parallel	
On-state Resistance	R _{oN}	$90 m\Omega$	$45 m\Omega$	
Nominal load current	I _{L(NOM)}	3.7A	7.4A	
Current limitation	$I_{L(SCr)}$	12A	12A	

Package



General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.
- Providing embedded protective functions

Applications

- μC compatible high-side power switch with diagnostic feedback for 12V and 24V grounded loads
- All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- · Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Improved electromagnetic compatibility (EMC)
- · Fast demagnetization of inductive loads
- Stable behaviour at undervoltage
- Wide operating voltage range
- · Logic ground independent from load ground

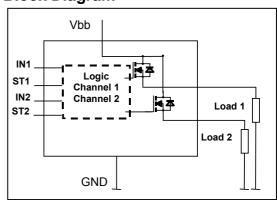
Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge protection (ESD)

Diagnostic Function

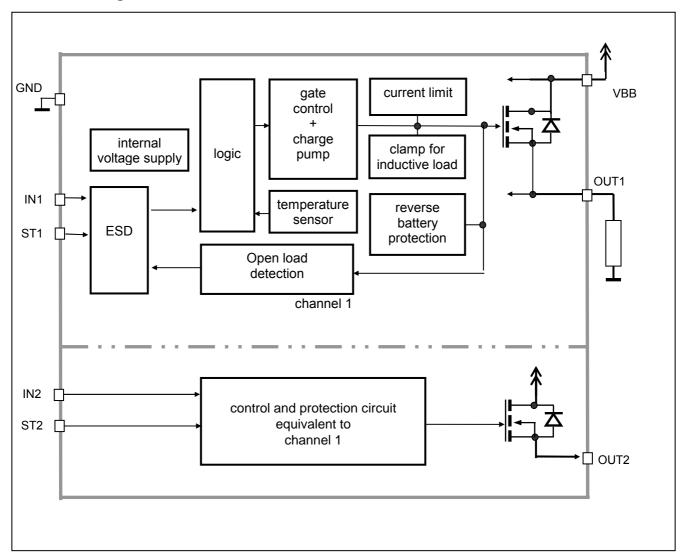
- · Diagnostic feedback with open drain output
- Open load detection in OFF-state
- Feedback of thermal shutdown in ON-state

Block Diagram





Functional diagram

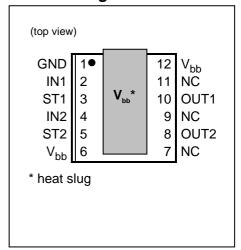




Pin Definitions and Functions

Pin	Symbol	Function
1	GND	Ground of chip
2	IN1	Input 1,2 activates channel 1,2 in case of logic
4	IN2	high signal
3	ST1	Diagnostic feedback 1 & 2 of channel 1,2
5	ST2	open drain, low on failure
6,12, heat slug	V _{bb}	Positive power supply voltage. Design the wiring for the simultaneous max. short circuit currents from channel 1 to 2 and also for low thermal resistance
7,9,11	NC	Not Connected
8	OUT2	Output 1,2 protected high-side power output
10	OUT1	of channel 1 and 2. Design the wiring for the max. short circuit current

Pin configuration





Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 6)	$V_{ m bb}$	43	V
Supply voltage for full short circuit protection $T_{j,start} = -40 \dots +150$ °C	V _{bb}	36	V
Load current (Short-circuit current, see page 6)	I ∟	self-limited	Α
Load dump protection ¹⁾ $V_{\text{LoadDump}} = V_{\text{A}} + V_{\text{S}}, \ V_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{(2)} = 2 \ \Omega, \ t_{\text{d}} = 400 \text{ ms}; \ \text{IN} = \text{low or high,}$ each channel loaded with $R_{\text{L}} = 13.5 \ \Omega,$	V _{Load dump} ³⁾	60	V
Operating temperature range	Tj	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55 + 150	
Power dissipation (DC) ⁴⁾ $T_a = 25$ °C:	P_{tot}	3.1	W
(all channels active) $T_a = 85$ °C:		1.6	
Maximal switchable inductance, single pulse $V_{bb} = 12V$, $T_{i,start} = 150$ °C ⁴⁾ , see diagrams on page 10			
$I_{L} = 3.5 \text{ A}, E_{AS} = 178 \text{ mJ}, 0\Omega$ one channel:	Z_{L}	21.3	mH
$I_L = 7.0 \text{ A}$, $E_{AS} = 337 \text{ mJ}$, 0Ω two parallel channels:		10	
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993 R=1.5kΩ; C=100pF	V _{ESD}	1.0 4.0 8.0	kV
Input voltage (DC) see internal circuit diagram page 9	V _{IN}	-10 +16	V
Current through input pin (DC)	I _{IN}	±0.3	mA
Pulsed current through input pin ⁵⁾	/ _{INp}	±5.0	
Current through status pin (DC)	I _{ST}	±5.0	

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Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150 Ω resistor for the GND connection is recommended.

²⁾ $R_{\rm I}$ = internal resistance of the load dump test pulse generator

³⁾ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

⁴⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

⁵⁾ only for testing



Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance						
junction - Case ⁶⁾	each channel:	R_{thjC}			5	K/W
junction – ambient ⁶⁾		$R_{\rm thja}$				
@ 6 cm ² cooling area	one channel active:			45		
	all channels active:			40		

Electrical Characteristics

Parameter and Conditions, each of the four channels	Symbol	Values			Unit
at $T_j = -40+150$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	
Load Switching Capabilities and Characteristics					
On-state resistance (V_{bb} to OUT); $I_L = 2 A$					
each channel, $T_j = 25$ °C: $T_j = 150$ °C:	Ron		70 140	90 180	mΩ
two parallel channels, $T_j = 25$ °C: see diagram, page 11			35	45	

see diagram, page 11	, ,					
Nominal load curren	t one channel active: two parallel channels active:	I _{L(NOM)}	3.7 7.4	4.7 9.5		Α
Device on PCB ⁶⁾ , $T_a =$	85°C, $T_j \le 150$ °C					
Output current while GND disconnected or pulled up ⁷⁾ ; Vbb = 32 V, VIN = 0,		I _{L(GNDhigh)}			2	mA
see diagram page 9						
Turn-on time8)	IN \int to 90% V_{OUT} :	<i>t</i> on		100	250	μs
Turn-off time	IN \square to 10% V_{OUT} :	$t_{ m off}$		100	270	
$R_{L} = 12 \Omega$						
Slew rate on 8)	10 to 30% V_{OUT} , $R_L = 12 \Omega$:	d V/dt _{on}	0.2		1.0	V/µs
Slew rate off 8)	70 to 40% V_{OUT} , $R_L = 12 \Omega$:	-d V/dt _{off}	0.2		1.1	V/µs

_

⁶⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

⁷⁾ not subject to production test, specified by design

⁸⁾ See timing diagram on page 12.



Parameter and Conditions, each of the four channels at T _j = -40+150°C, V _{bb} = 12 V unless otherwise specified		Symbol		Values	Values		
			min	typ	max		
Operating Parameters							
Operating voltage		$V_{ m bb(on)}$	5.5		40	V	
Undervoltage switch off ⁹)	T _j =-40°C25°C:	V _{bb(u so)}			4.5	V	
	<i>T</i> _j =125°C:				4.5 ¹⁰⁾		
Overvoltage protection ¹¹⁾ $I_{bb} = 40 \text{ mA}$		$V_{\mathrm{bb}(AZ)}$	41	47	52	V	
Standby current ¹²)	T _j =-40°C25°C:	I _{bb(off)}		4.5	10	μΑ	
$V_{IN} = 0$; see diagram page 11	$T_{\rm j}$ =150°C:				15		
	<i>T</i> _j =125°C:				10 ¹⁰⁾		
Off-State output current (included in $I_{bb(off)}$) $V_{IN} = 0$; each channel		I _{L(off)}		1	5	μΑ	
Operating current ¹³⁾ , $V_{IN} = 5V$,		_				_	
	one channel on: all channels on:	I _{GND}		0.6 1.2	1.2 2.4	mA	
Protection Functions ¹⁴⁾							
Current limit, Vout = 0V, (see timing dia	agrams, page 12)						
 -	$T_{\rm j}$ =-40°C: $T_{\rm j}$ =25°C:	I _{L(lim)}			23	Α	
	<i>T</i> j =25°C: <i>T</i> i =+150°C:			15			
	/ _j =+150 C.		9				
Repetitive short circuit current limi	t,						
$T_{\rm j} = T_{\rm jt}$	each channel two channels	/L(SCr)		12 12		А	
(see timing diagrams, page 12)							
Initial short circuit shutdown time	$T_{j,start} = 25$ °C:	toff(SC)		2		ms	
V _{out} = 0V (see timing di	agrams on page 12)						
Output clamp (inductive load switch off) ¹⁵⁾ at VON(CL) = Vbb - VOUT, IL = 40 mA		V _{ON(CL)}	41	47	52	V	
Thermal overload trip temperature		T_{jt}	150			°C	
Thermal hysteresis		$\Delta T_{\rm jt}$		10		K	

⁹⁾ is the voltage, where the device doesn't change it's switching condition for 15ms after the supply voltage falling below the lower limit of Vbb(on)

¹⁰⁾ not subject to production test, specified by design

Supply voltages higher than V_{bb(AZ)} require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended). See also V_{ON(CL)} in table of protection functions and circuit diagram on page 9.

¹²⁾ Measured with load; for the whole device; all channels off

¹³⁾ Add I_{ST} , if $I_{ST} > 0$

Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹⁵⁾ If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest VON(CL)



Parameter and Conditions, each of the four channels		Symbol	Values		i	Unit
at $T_j = -40+150$ °C, $V_{bb} = 12 \text{ V unless}$	s otherwise specified		min	typ	max	
Reverse Battery						
Reverse battery voltage 16)		- V _{bb}			32	V
Drain-source diode voltage (V_{out} $I_L = -2.0 \text{ A}$, $T_j = +150 ^{\circ}\text{C}$	t > Vbb)	-V _{ON}		600		mV
Diagnostic Characteristics						
Open load detection voltage		V _{OUT(OL)}	1.7	2.8	4.0	V
Input and Status Feedback ¹⁷)						
Input resistance (see circuit page 9)		R_{l}	2.5	4.0	6.0	kΩ
Input turn-on threshold voltage		$V_{\text{IN(T+)}}$			2.5	V
Input turn-off threshold voltage		$V_{\text{IN(T-)}}$	1.0			V
Input threshold hysteresis		$\Delta V_{\rm IN(T)}$		0.2		V
Status change after positive input slope ¹⁸⁾ with open load		t _{d(STon)}		10	20	μS
Status change after positive input slope ¹⁸⁾ with overload		t _{d(STon)}	30			μS
Status change after negative input slope with open load		t _{d(SToff)}			500	μS
Status change after negative input slope ¹⁸⁾		t _{d(SToff)}			20	μS
with overtemperature		, ,				
Off state input current	$V_{IN} = 0.4 \text{ V}$:	I _{IN(off)}	5		20	μΑ
On state input current $V_{IN} = 5 \text{ V}$:		I _{IN(on)}	10	35	60	μΑ
Status output (open drain)						
Zener limit voltage	$I_{ST} = +1.6 \text{ mA}$:	$V_{\rm ST(high)}$	5.4			V
ST low voltage	$I_{ST} = +1.6 \text{ mA}$:	$V_{\rm ST(low)}$			0.6	

Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 4 and circuit page 9).

 $^{^{17)}}$ If ground resistors $R_{\mbox{\footnotesize GND}}$ are used, add the voltage drop across these resistors.

¹⁸⁾ not subject to production test, specified by design



Truth Table

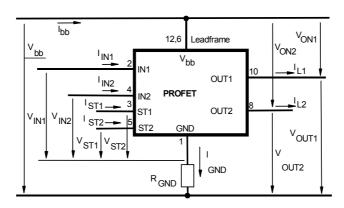
(each channel)

	IN	OUT	ST
Normal operation	L	L	Н
	Н	Н	Н
Open load	L	Z	լ19)
	Н	Н	Н
Overtemperature	L	L	Н
	Н	L	L

L = "Low" Level X = don't care Z = high impedance, potential depends on external circuit X = H = "High" Level Status signal valid after the time delay shown in the timing diagrams

Parallel switching of channel 1 and 2 is easily possible by connecting the inputs and outputs in parallel (see truth table). If switching channel 1 to 2 in parallel, the status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor.

Terms



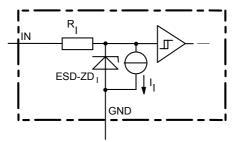
Leadframe (V_{bb}) is connected to pin 6,12

External R_{GND} optional; single resistor R_{GND} = 150 Ω for reverse battery protection up to the max. operating voltage.

¹⁹⁾ L, if potential at the Output exceeds the OpenLoad detection voltage

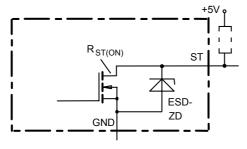


Input circuit (ESD protection), IN1 or IN2



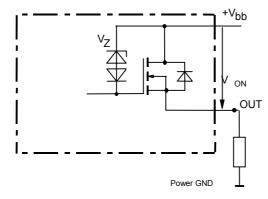
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Status output, ST1 or ST2



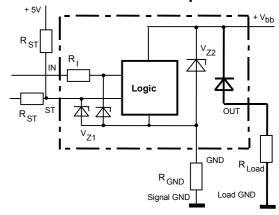
ESD-Zener diode: 6.1 V typ., max 0.3 mA; $R_{ST(ON)}$ < 375 Ω at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp, OUT1 or OUT2



 V_{ON} clamped to $V_{ON(CL)} = 47 \text{ V typ.}$

Overvolt. and reverse batt. protection

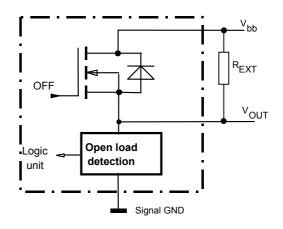


 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_{I} = 3.5 kΩ typ.

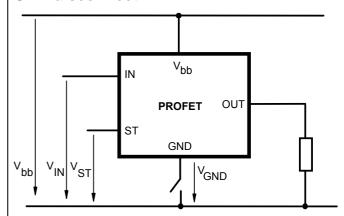
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

Open-load detection, OUT1 or OUT2

OFF-state diagnostic condition: Open Load, if $V_{OUT} > 3 \text{ V typ.}$; IN low



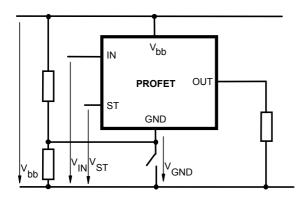
GND disconnect



Any kind of load. In case of IN=high is $VOUT \approx VIN - VIN(T+)$. Due to VGND > 0, no VST = low signal available.

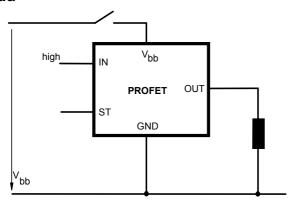


GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no $V_{ST} = low$ signal available.

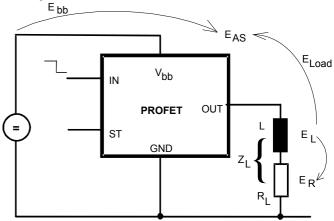
V_{bb} disconnect with energized inductive load



For inductive load currents up to the limits defined by $Z_{\rm L}$ (max. ratings and diagram on page 10) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = \frac{1}{2} \cdot L \cdot I_1^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

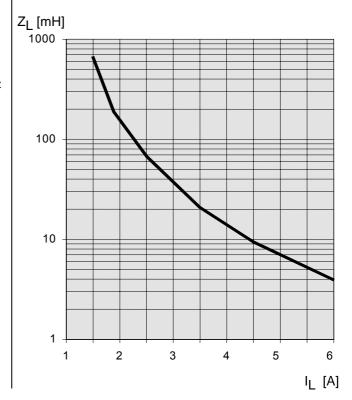
$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) ln (1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|})$$

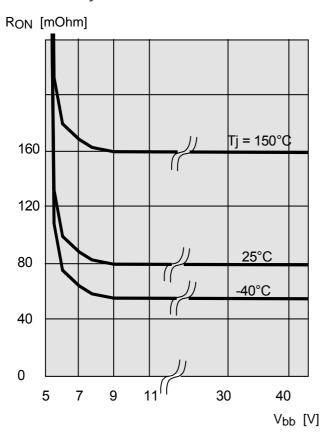
Maximum allowable load inductance for a single switch off (one channel)⁴⁾

$$L = f(I_L)$$
; T_{j,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω



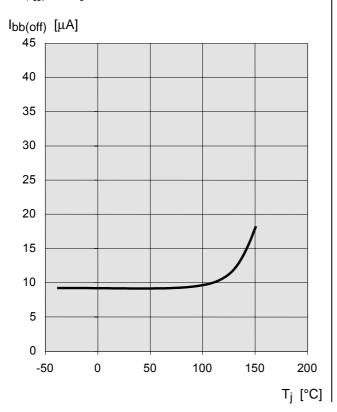


Typ. on-state resistance $RoN = f(V_{bb}, T_j)$; $I_L = 2 \text{ A}$, IN = high



Typ. standby current

 $I_{bb(off)} = f(T_j); V_{bb} = 9...34 \text{ V}, IN1,2 = low$





Timing diagrams

All channels are symmetric and consequently the diagrams are valid for channel 1 to channel 4

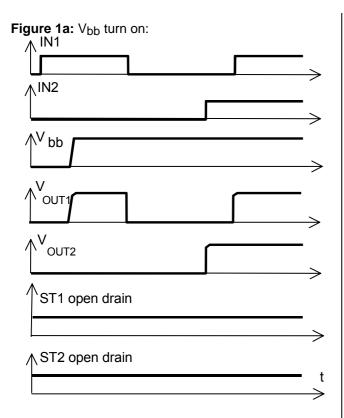


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:

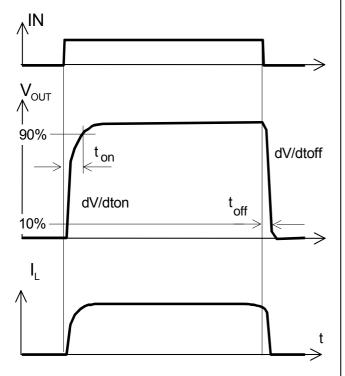


Figure 2b: Switching a lamp:

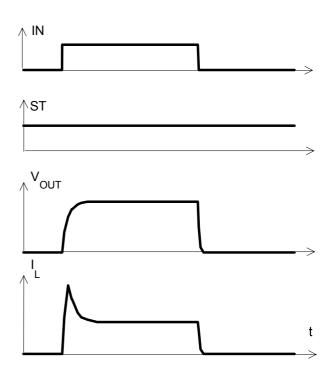
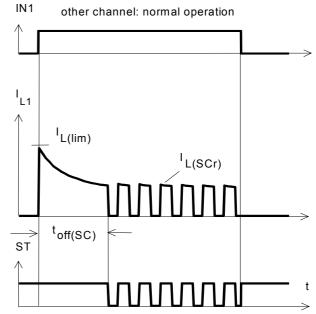


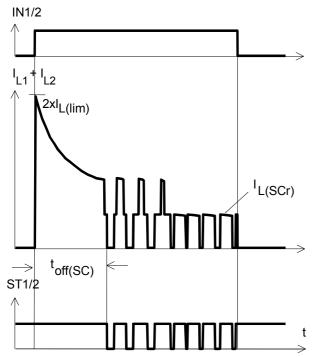
Figure 3a: Turn on into short circuit: shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions



Figure 3b: Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)



ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor.

Figure 4a: Overtemperature: Reset if $T_i < T_{it}$

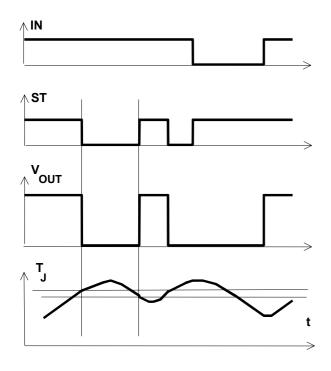


Figure 5a: Open load: detection in OFF-state, turn on/off to open load

Open load of channel 1; other channels normal operation

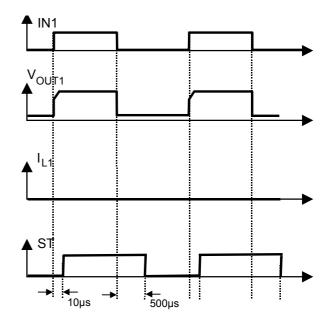
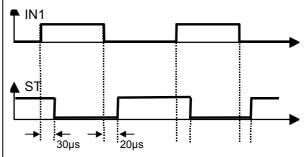


Figure 6a: Status change after, turn on/off to overtemperature

Overtemperature of channel 1; other channels normal operation

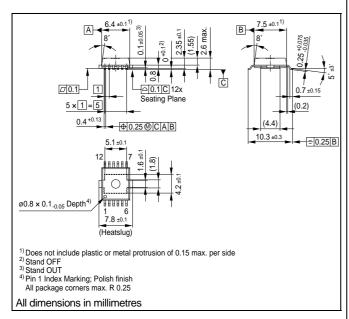




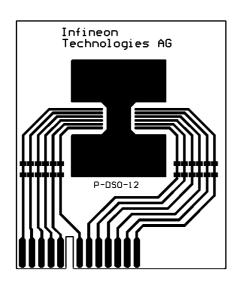
Package and Ordering Code

Standard: P-DSO-12-2

Sales Code	BTS 5215L
Ordering Code	Q67060-S7023



Printed circuit board (FR4, 1.5mm thick, one layer $70\mu m$, $6cm^2$ active heatsink area) as a reference for max. power dissipation P_{tot} , nominal load current $I_{L(NOM)}$ and thermal resistance R_{thia}



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